

**B.Tech. - VIEP - ELECTRONICS AND  
COMMUNICATION ENGINEERING  
(BTECVI)**

**Term-End Examination**

**June, 2015**

00126

**BIEL-012 : ANALOG AND MIXED MODE VLSI  
DESIGN**

*Time : 3 hours*

*Maximum Marks : 70*

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*Note : Attempt any **seven** questions. All questions carry equal marks. Assume suitable missing data, if any. Use of scientific calculator is permitted.*

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1. Explain the following terms of op-amp :  $4 \times 2 \frac{1}{2} = 10$
- (a) CMRR
  - (b) Slew Rate
  - (c) PSRR
  - (d) Gain
2. Design a multiplier using squaring circuits. How is it different from multiplying quad approach ? 10

3. (a) Which is the most basic DAC architecture ? Explain its basic operation principle.
- (b) Design a 3-bit DAC using an R-2R architecture with  $R = 1 \text{ k}\Omega$ ,  $R_F = 2 \text{ k}\Omega$  and  $V_{REF} = 5 \text{ V}$ . Assume that the resistances of the switches are negligible. Determine the value of  $i_{TOTAL}$  for each digital input and the corresponding output voltage,  $V_{out}$ .  $2 \times 5 = 10$
4. (a) Explain the pipeline architecture of ADC.
- (b) Differentiate between single-slope ADC and dual-slope ADC. Explain them with block diagrams.  $2 \times 5 = 10$
5. Explain the operation principle of a two-stage op-amp. What is the need of compensation in op-amp ? How do you estimate the bandwidth in op-amp circuits ?  $10$
6. Explain the operation principle of band-pass and high-pass sync filters. How is it different from interpolating filters ?  $7 + 3 = 10$
7. (a) Draw the process flow of sub-micron CMOS technology for inverter circuits.
- (b) How is MOS capacitor fabricated and characterized ? Explain with suitable process flow diagrams.  $2 \times 5 = 10$

8. (a) What are the short-channel effects in MOSFET? How can these be avoided?
- (b) Draw the small-signal models of MOSFET considering channel length modulation and body effect by a dependent current source or/and by a resistor. 2×5=10
9. (a) Consider the amplifier as shown in Figure 1, with  $(W/L)_{1-4} = 50/0.5$ ,  $I_{SS} = 1 \text{ mA}$ , and input CM level of 1.3 V. Calculate the small-signal gain and the maximum output swing if all transistors remain in saturation.

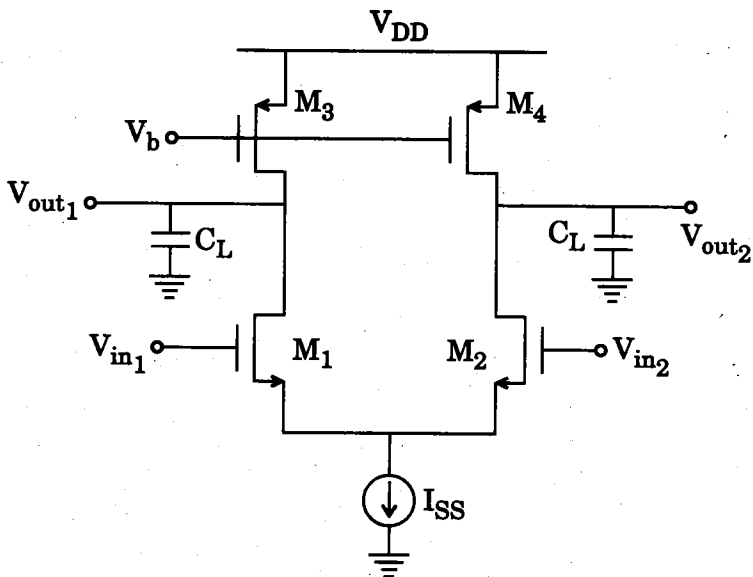


Figure 1

- (b) Suppose all PMOS enters into the triode region by 50 mV, so as to increase the allowable differential swing by 100 mV. What is the small-signal gain at the peaks of the output swing ?

7+3=10

10. Write short notes on any *two* of the following :

2×5=10

- (a) S/H Characteristics
  - (b) Flash ADC
  - (c) Cyclic DAC
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